Part Number	Customer

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	100.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110}+/-1 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none	
	5.0	Overall Thickness	444.00 +/- 5.00 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<3.00µm	Guaranteed by Process
	7.0	Bow	<80.00µm	ADE to ASTM F534, 20%
	8.0	Warp	<80.00µm	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	13.0	Handle Thickness	350.00 +/- 2.00 µm	ADE, 100%
	14.0	Handle Doping Type	N	Wafer Vendor
	15.0	Handle Dopant	Phosphorous	Wafer Vendor
	16.0	Handle Resistivity	1 - 10 Ohmcm	Wafer Vendor
	17.0	Backside Finish	Polished with oxide and laser mark. Oxide thickness expected between 40000A and 63000A	Wafer Vendor
BuriedOxide	18.0	Oxide Type	Thermal	
	19.0	Oxide Thickness	60,000.00 +/- 3,000.00 A	Nanospec centre point, 4%
	20.0	Oxide formed on	Handle Wafer only	
DeviceSilicon	21.0	Device Growth Method	CZ	Wafer Vendor
	22.0	Device Orientation	{100} +/- 1 degree	Wafer Vendor
	23.0	Nominal Thickness	70.00 +/- 0.50 µm	FTIR, 100% 9-Pt (note3)
	24.0	Distance to device silicon edge from wafer edge	<= 2mm	Typical by Process
	25.0	Device Doping Type	N	Wafer Vendor
	26.0	Device Dopant	Phosphorous	Wafer Vendor
	27.0	Device Resistivity	1 - 10 Ohmcm	Wafer Vendor
BuriedOxide2	28.0	Oxide 2 Type	Thermal	
	29.0	Oxide 2 Thickness	30,000.00 +/- 1,500.00 A	Nanospec centre point measurement, 4%
	30.0	Oxide 2 formed on	Device 2 wafer	Guaranteed by Process
DeviceSilicon2	31.0	Device 2 Growth Method	CZ	Wafer Vendor
	32.0	Device 2 Orientation	{100} +/- 1 degree	Wafer Vendor
	33.0	Device 2 Nominal Thickness	15.00 +/- 0.50 um	FTIR, 100% 9-point measurement (see note 3)

Part Number Customer

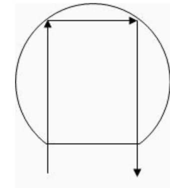
Category		Parameter	Specification	Measurement Method
DeviceSilicon2	34.0	Distance to Device 2 edge from wafer edge	< = 4mm	Guaranteed by Process
	35.0	Device 2 DopingType	N	Wafer Vendor
	36.0	Device 2 Dopant	Phosphorous	Wafer Vendor
	37.0	Device 2 Resistivity	1 - 10 Ohmcm	Wafer Vendor
DeviceSilicon	41.0	Voids	none	Wafer Vendor
	42.0	Scratches	0	Bright Light, 100% (note 2)
	43.0	Haze	none	Bright Light, 100% (note 2)
	44.0	Device Field Oxidation	7,000.00 +/- 350.00 A	Nanospec 4%, 5pt

Part Number	Customer

Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

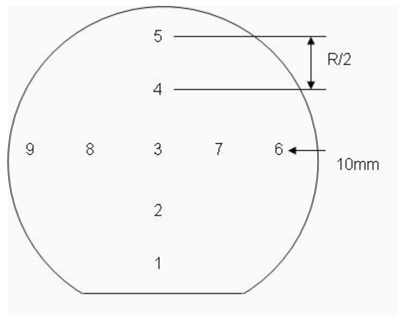
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information